Old Company Name in Catalogs and Other Documents

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April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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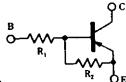


COMPOUND TRANSISTOR

on-chip resistor PNP silicon epitaxial transistor For mid-speed switching

FEATURES

- Up to 0.7 A current drive available
- On-chip bias resistor
- Low power consumption during drive



QUALITY GRADES

Standard

Please refer to "Quality Grades on NEC Semiconductor Devices" (Document No. C11531E) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

FP1 SERIES LISTS

Products	Marking	R1 (KΩ)	R2 (KΩ)
FP1A4A	S30	-	10
FP1L2Q	S31	0.47	4.7
FP1A3M	S32	1.0	1.0
FP1F3P	S33	2.2	10
FP1J3P	S36	3.3	10
FP1L3N	S34	4.7	10
FP1A4M	S35	10	10

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vсво	-25	V
Collector to emitter voltage	VCEO	-25	V
Emitter to base voltage	Vebo	-10	V
Collector current (DC)	IC(DC)	-0.7	А
Collector current (Pulse)	C(pulse) *	-1.0	А
Base current (DC)	IB(DC)	-20	mA
Total power dissipation	Ρτ	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

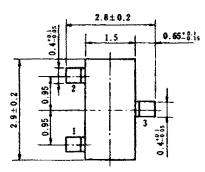
* PW \leq 10 ms, duty cycle \leq 50 %

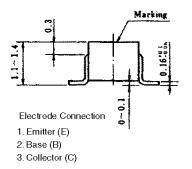
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Document No. D16181EJ1V0DS00 (1st edition) Date Published April 2002 N CP(K) Printed in Japan

PACKAGE DRAWING (UNIT: mm)





FP1A4A ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -22 V, I_E = 0$			-100	nA
DC current gain	hfe1 **	Vce = -2.0 V, Ic = -0.1 A	200			-
DC current gain	hFE2 **	Vce = -2.0 V, Ic = -0.5 A	100			-
DC current gain	hfe3 **	Vce = -2.0 V, Ic = -0.7 A	50			-
Collector saturation voltage	VCE(sat) **	Ic = -0.3 A, Iв = -6 mA		0.28	0.4	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$			-0.3	V
Input resistance	R1		-	_	-	Ω
E-to-B resistance	R ₂		7	10	13	kΩ

** PW \leq 350 μ s, duty cycle \leq 2 %

FP1L2Q ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -22 V, I_E = 0$			-100	nA
DC current gain	hFE1 **	Vce = -2.0 V, Ic = -0.1 A	150	350		-
DC current gain	hFE2 **	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -0.5 \text{ A}$	100	300		-
DC current gain	hfe3 **	Vce = -2.0 V, Ic = -0.7 A	50	200		-
Low level output voltage	Vol **	V _{IN} = -5.0 V, Ic = -0.3 A		-0.3	-0.4	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$		-0.65	-0.3	V
Input resistance	R1		329	470	611	Ω
E-to-B resistance	R ₂		3.29	4.7	6.11	kΩ

** PW \leq 350 μ s, duty cycle \leq 2 %

FP1A3M

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -22 V, I_E = 0$			100	nA
DC current gain	hfe1 **	Vce = -2.0 V, Ic = -0.1 A	80			I
DC current gain	hFE2 **	Vce = -2.0 V, Ic = -0.5 A	100			-
DC current gain	hfe3 **	Vce = -2.0 V, Ic = -0.7 A	50			-
Low level output voltage	Vol **	$V_{IN} = -5.0 \text{ V}, \text{ Ic} = -0.2 \text{ A}$		-0.3	-0.4	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$			-0.3	V
Input resistance	R1		0.7	1.0	1.3	kΩ
E-to-B resistance	R2		0.7	1.0	1.3	kΩ

** PW \leq 350 μ s, duty cycle \leq 2 %

FP1F3P ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	Vсв = -22 V, IE = 0			-100	nA
DC current gain	hfe1 **	Vce = -2.0 V, Ic = -0.1 A	200			-
DC current gain	hFE2 **	Vce = -2.0 V, Ic = -0.5 A	100			-
DC current gain	hfe3 **	Vce = -2.0 V, Ic = -0.7 A	50			_
Low level output voltage	Vol **	V _{IN} = -5.0 V, Ic = -0.2 A			-0.4	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$			-0.3	V
Input resistance	R1		1.54	2.2	2.86	kΩ
E-to-B resistance	R ₂		7	10	13	kΩ

** PW \leq 350 μ s, duty cycle \leq 2 %

FP1J3P

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V _{CB} = -22 V, I _E = 0			-100	nA
DC current gain	hfe1 **	Vce = -2.0 V, Ic = -0.1 A	200	470		-
DC current gain	hfe2 **	Vce = -2.0 V, Ic = -0.5 A	100	300		-
DC current gain	hfe3 **	$V_{CE} = -2.0 V$, $I_C = -0.7 A$	50	200		_
Low level output voltage	Vol **	V _{IN} = −5.0 V, Ic = −150 mA		-0.2	-0.4	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$		-0.65	-0.3	V
Input resistance	R1		2.3	3.3	4.3	kΩ
E-to-B resistance	R2		7	10	13	kΩ

** PW \leq 350 μ s, duty cycle \leq 2 %

FP1L3N ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -22 V, I_E = 0$			-100	nA
DC current gain	hfe1 **	Vce = -2.0 V, Ic = -0.1 A	200			1
DC current gain	hfe2 **	Vce = -2.0 V, Ic = -0.5 A	100			-
DC current gain	hfe3 **	Vce = -2.0 V, Ic = -0.7 A	50			-
Low level output voltage	Vol **	V _{IN} = -5.0 V, Ic = -150 mA			-0.45	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$			-0.3	V
Input resistance	R1		3.29	4.7	6.11	kΩ
E-to-B resistance	R ₂		7	10	13	kΩ

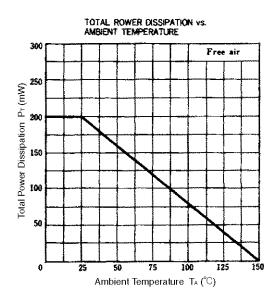
** PW \leq 350 μ s, duty cycle \leq 2 %

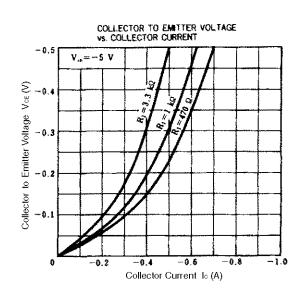
FB1A4M ELECTRICAL CHARACTERISTICS (Ta = 25°C)

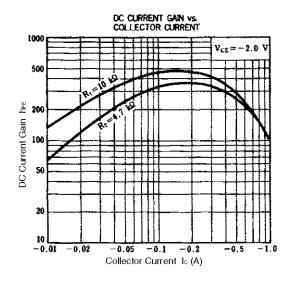
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -22 V, I_E = 0$			-100	nA
DC current gain	hfe1 **	Vce = -2.0 V, Ic = -0.1 A	200			-
DC current gain	hFE2 **	$V_{CE} = -2.0 \text{ V}, \text{ Ic} = -0.5 \text{ A}$	100			-
DC current gain	hfe3 **	Vce = -2.0 V, Ic = -0.7 A	50			-
Collector saturation voltage	VCE(sat) **	V _{IN} = -5.0 V, Ic = -0.1 A			-0.4	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$			-0.3	V
Input resistance	R1		7	10	13	kΩ
E-to-B resistance	R2		7	10	13	kΩ

** PW \leq 350 μ s, duty cycle \leq 2 %

TYPICAL CHARACTERISTICS (Ta = 25°C)







COLLECTOR SATURATON VOLTAGE vs. COLLECTOR CURRENT

-0.05

-0.2

-0.1

Collector Current Ic (A)

Collector Saturation Voltage Voresati (V)

-0.02

-0.01

-0.01 -0.02

-1.0

0.5

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact an NEC sales representative.

Surface MOUNTING TYPE

For details of the recommended soldering conditions, refer to the document Semiconductor Device Mounting Technology Manual (C10535E).

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 230°C, Time: 30 sec. max. (at 210°C or higher), Count: Once, Exposure limit: None *	IR30-00
VPS	Package peak temperature: 215°C, Time: 40 sec. max. (at 200°C or higher), Count: Once, Exposure limit: None *	VP15-00
Partial heating	Pin temperature: 300°C max., Time: 10 sec. max. Exposure limit: None *	0

* After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Cautions 1. Do not use different soldering methods together (except for partial heating).

2. Prevent the resin surface temperature from being higher than the board temperature by 20°C or more.

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